

ABSTRACT OF THE DISCLOSURE

A manufacturing method for a buried insulating layer-type semiconductor silicon carbide substrate comprises the step of placing an SOI substrate 100, which has a surface silicon layer 130 of a predetermined thickness and a buried insulator 120, in a heating furnace 200 and of increasing the temperature of the atmosphere within heating furnace 200 while supplying a mixed gas (G1+G2) of a hydrogen gas G1 and of a hydrocarbon gas G2 into heating furnace 200, thereby, of metamorphosing surface silicon layer 130 of SOI substrate 100 into a single crystal silicon carbide thin film 140.